Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	10741	((438/149) or (438/151) or (438/164) or (438/166) or (438/311) or (438/412) or (438/378) or (438/479) or (438/482) or (438/486) or (438/487) or (438/488) or (438/489) or (438/490) or (438/595) or (438/596) or (438/704) or (438/406) or (438/735) or (438/745) or (438/764) or (438/795) or (438/800) or (438/902)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/13 15:38
L2	121	1 and ((polysilicon near spacer$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 16:13
L3	0	1 and ((polysilicon near spacer$1) near (active adj (layer$1 or film$1)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 15:53
L4	1	1 and ((polysilicon near spacer$1) same (active adj (layer$1 or film$1)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 15:57
L5	0	((polysilicon near spacer$1) near (active adj (layer$1 or film$1)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 15:53
L6	4	((polysilicon near spacer$1) same (active adj (layer$1 or film$1)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 15:55
L7	16	((polysilicon near spacer$1) and (active adj (layer$1 or film$1)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 15:55

L8	0	1 and ((polysilicon near sidewll near spacer$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 15:57
L9	33	1 and ((polysilicon near sidewall near spacer$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 16:04
L10	1	9 and (active adj (layer$1 or film$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 15:58
L11	10473	(polysilicon near$3 spacer$1) same (active near2 (layer$1 or film$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 16:06
L12	2040	(polysilicon near$3 spacer$1) near (active near2 (layer$1 or film$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 16:06
L13	0	(polysilicon near spacer$1) near (active near2 (layer$1 or film$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 16:06
L14	34	(polysilicon near spacer$1) same (active near2 (layer$1 or film$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 16:10
L15	153	(polysilicon near spacer$1) and (active near2 (layer$1 or film$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/13 16:10

S1	10057	((438/149) or (438/151) or (438/164) or (438/166) or (438/311) or (438/412) or (438/378) or (438/479) or (438/482) or (438/486) or (438/487) or (438/488) or (438/489) or (438/490) or (438/595) or (438/596) or (438/704) or (438/406) or (438/735) or (438/745) or (438/764) or (438/795) or (438/800) or (438/902)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/13 15:38
S2	12	(("4330363") or ("4592799") or ("5021119") or ("5395481") or ("6495405")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/08 23:06
S3	2901	((polycrystalline near2 silicon) or (poly adj silicon)) near2 (tft or ((thin near2 film) near2 transistor$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 17:34
S4	1053	((polycrystalline near2 silicon) or (poly adj silicon)) near3 (spacer$1 or sidewall$1 or (sidewall near2 spacer$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 21:19
S5	8	S3 and S4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 17:36
S6	1	S1 and S5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 17:36
S7	1152	((polycrystalline near2 silicon) or (poly adj silicon)) near3 (spacer$1 or sidewall$1 or capp$3 or (capp$3 near2 (layer or film)) or (sidewall near2 spacer$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 18:04

S8	4082	S7 and3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 17:39
S9	12	S7 and S3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 17:39
S10	1	S9 and S1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 17:39
S11	11	S9 not S10	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 17:40
S12	16	((polycrystalline near2 silicon) or (poly adj silicon)) near3 (spacer$1 or sidewall$1 or (sidewall near2 spacer$1)) same (active near2 (layer$1 or film$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 17:44
S13	16	((polycrystalline near2 silicon) or (poly adj silicon)) near3 (spacer$1 or sidewall$1 or capp$3 or (capp$3 near2 (layer or film)) or (sidewall near2 spacer$1)) same (active near2 (layer$1 or film$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 17:54
S14	6	((polycrystalline near2 silicon) or (poly adj silicon)) near3 (spacer$1 or sidewall$1 or capp$3 or (capp$3 near2 (layer or film)) or (sidewall near2 spacer$1)) near10 (active near2 (layer$1 or film$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 17:52
S15	10	S13 not S14	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 17:52
S16	0	("2004/0026738").URPN.	USPAT	OR	OFF	2004/12/08 17:53

S17	123	((polycrystalline near2 silicon) or (poly adj silicon)) near3 (spacer$1 or sidewall$1 or capp$3 or (capp$3 near2 (layer or film)) or (sidewall near2 spacer$1))and (active near2 (layer$1 or film$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 17:55
S18	107	S17 not S13	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 17:55
S19	33	((polycrystalline near2 silicon) or (poly adj silicon)) near3 (spacer$1 or sidewall$1 or capp$3 or (capp$3 near2 (layer or film)) or (sidewall near2 spacer$1)) same (crystall$7 or recrystall$7)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 18:05
S20	7	S19 and (active near2 (layer$1 or film$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 18:07
S21	0	S19 not S7	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 18:08
S22	26	S19 not S20	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 18:09
S23	106	((LTPS adj TFT) or (low adj temperature adj polycrystalline adj silicon adj thin adj film adj transistor))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 21:21

S24	10057	((438/149) or (438/151) or (438/164) or (438/166) or (438/311) or (438/412) or (438/378) or (438/479) or (438/482) or (438/486) or (438/487) or (438/488) or (438/489) or (438/490) or (438/595) or (438/596) or (438/704) or (438/406) or (438/735) or (438/745) or (438/764) or (438/795) or (438/800) or (438/902)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/08 21:21
S25	103	S23 and "1"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 21:26
S26	21	S23 and S24	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 21:22
S27	75	S23 and (amorphous)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 22:30
S28	19	S27 and S24	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 21:26
S29	42860	(spc or (solid adj phas adj crystallization)) or (milc or (metal adj induced adj lateral adj crystallization)) or (ela or (excimer adj laser adj annealing))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 22:33
S30	27	S29 and S23	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 22:33
S31	0	("2004/0217424").URPN.	USPAT	OR	OFF	2004/12/08 22:38
S32	1	("6242292").PN.	USPAT	OR	OFF	2004/12/08 22:38

S33	52	("3848104" | "4046618" | "4059461" | "4083272" | "4160263" | "4234358" | "4249960" | "4266986" | "4309225" | "4328553" | "4341569" | "4370175" | "4439245" | "4463028" | "4468551" | "4469551" | "4545823" | "4734550" | "4764485" | "4803528" | "4835704" | "4862227" | "4937618" | "4942058" | "4956539" | "4970366" | "5217921" | "5219786" | "5221365" | "5247375" | "5313076" | "5352291" | "5365875" | "5372836" | "5413958" | "5424230" | "5424244" | "5432122" | "5477073" | "5561081" | "5572046" | "5578520" | "5589406" | "5612251" | "5622814" | "5648277" | "5696003" | "5708252" | "5712191" | "5736414" | "5756364" | "5858473").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2004/12/08 22:40
S34	20	(("5365080") or ("5847419") or ("6607948") or ("6674100") or ("5063166") or ("4962051") or ("4962051") or ("4914053") or ("4868614")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/08 23:10
S35	2	("5818053").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/08 23:10